

40V +175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET
Product Summary

$V_{(BR)DSS}$	$R_{DS(on) \max}$	I_D $T_A = +25^\circ\text{C}$
40V	15mΩ @ $V_{GS} = 10\text{V}$	8.6A
	20mΩ @ $V_{GS} = 4.5\text{V}$	7.5A

Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low $R_{DS(ON)}$ – Minimizes Power Losses
- Low Qg – Minimizes Switching Losses
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

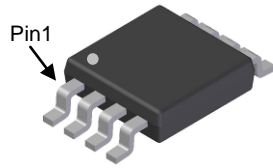
Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

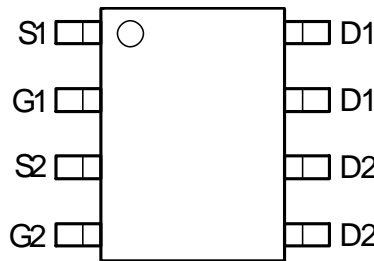
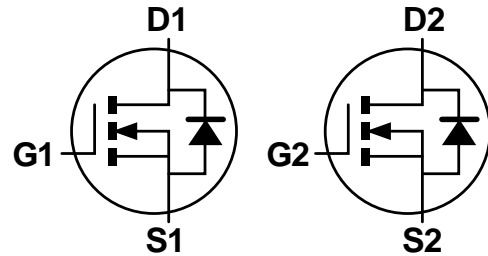
- Engine Management Systems
- Body Control
- DC-DC Converters

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 Ⓔ3
- Weight: 0.074 grams (Approximate)



Top View

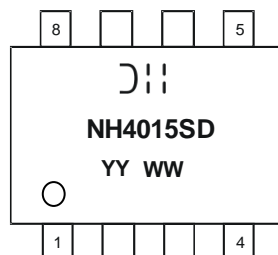

 Top View
Pin Configuration


Equivalent Circuit

Ordering Information (Note 5)

Part Number	Case	Packaging
DMNH4015SSDQ-13	SO-8	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
 5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information


⌋⌋ = Manufacturer's Marking
 NH4015SD = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 16 = 2016)
 WW = Week (01 - 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	40	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 7) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	8.6 6.9	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	11.0 8.8	A
Maximum Body Diode Forward Current (Note 7)			I _S	2.2	A
Pulsed Drain Current (380µs pulse, duty cycle = 1%)			I _{DM}	80	A
Avalanche Current (Note 8) L = 0.1mH			I _{AS}	25	A
Avalanche Energy (Note 8) L = 0.1mH			E _{AS}	33	mJ

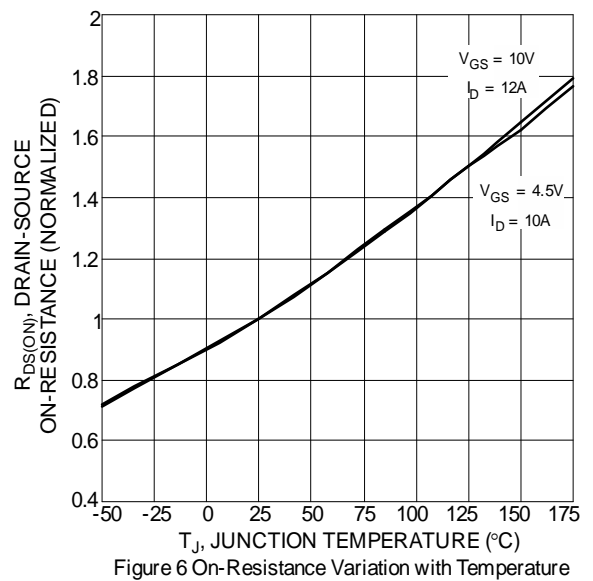
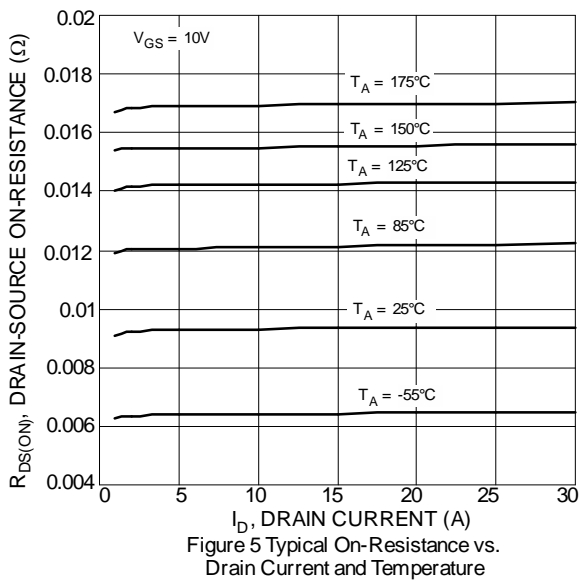
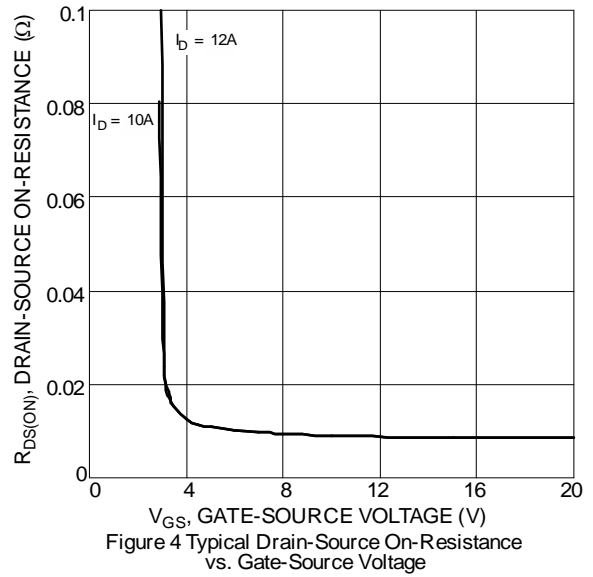
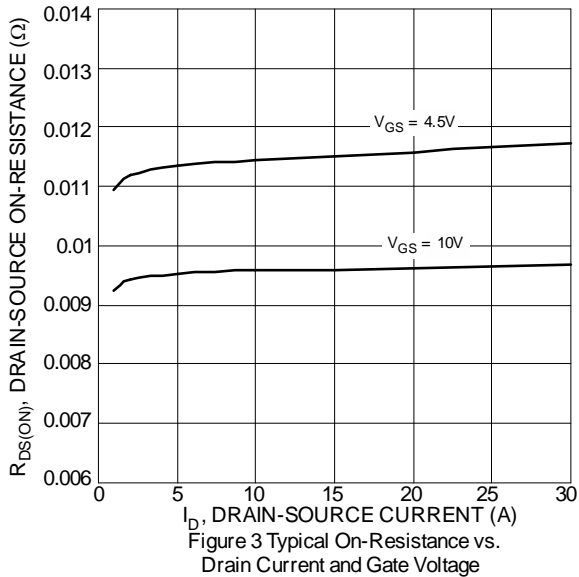
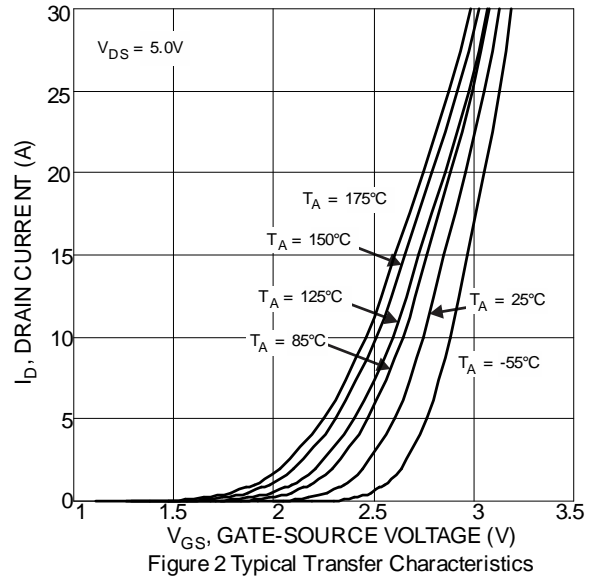
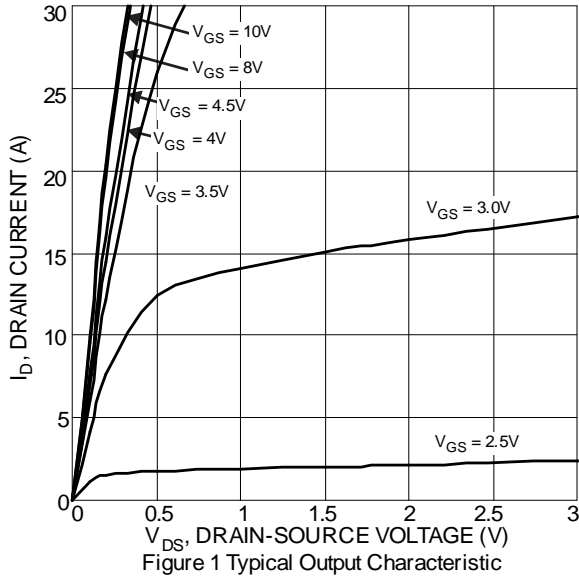
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.4	W
	T _A = +70°C		0.9	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R _{θJA}	111	°C/W
	t < 10s		66	
Total Power Dissipation (Note 7)	T _A = +25°C	P _D	2.0	W
	T _A = +70°C		1.2	
Thermal Resistance, Junction to Ambient (Note 7)	Steady state	R _{θJA}	75	°C/W
	t < 10s		45	
Thermal Resistance, Junction to Case (Note 7)		R _{θJC}	10.4	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	40	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 40V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	10	15	mΩ	V _{GS} = 10V, I _D = 12A
		—	12	20		V _{GS} = 4.5V, I _D = 10A
Diode Forward Voltage	V _{SD}	—	0.7	1.0	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	1,938	-	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	156	-		
Reverse Transfer Capacitance	C _{rss}	—	126	-		
Gate Resistance	R _G	—	1.8	3.2	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	15	-	nC	V _{DS} = 15V, I _D = 12A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	33	-		
Gate-Source Charge	Q _{gs}	—	4.4	-		
Gate-Drain Charge	Q _{gd}	—	5.9	-		
Turn-On Delay Time	t _{D(on)}	—	4.4	-	nS	V _{DD} = 15V, V _{GS} = 10V, R _L = 1.25Ω, R _G = 3Ω,
Turn-On Rise Time	t _r	—	10.5	-		
Turn-Off Delay Time	t _{D(off)}	—	12.3	-		
Turn-Off Fall Time	t _f	—	5.7	-		
Body Diode Reverse Recovery Time	t _{rr}	—	11	—	nS	I _S = 12A, di/dt = 500A/µs
Body Diode Reverse Recovery Charge	Q _{rr}	—	7.6	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
 - I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.



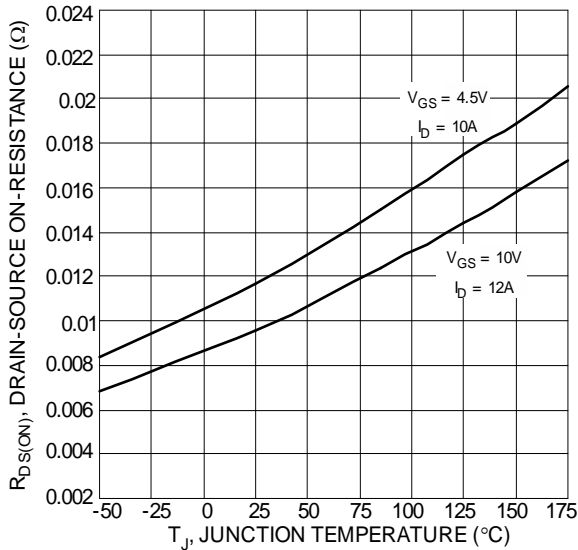


Figure 7 On-Resistance Variation with Temperature

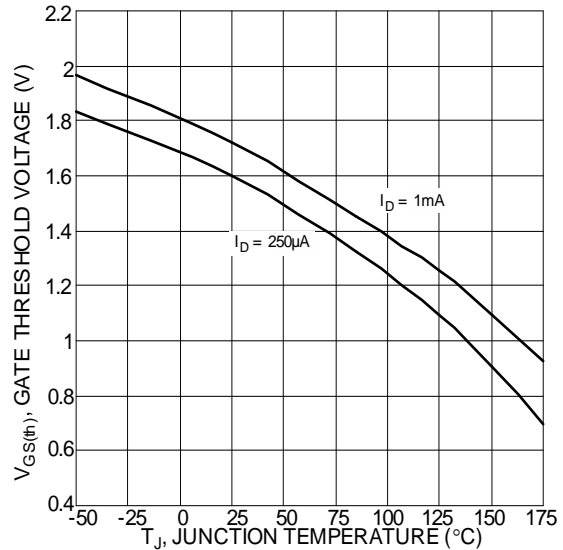


Figure 8 Gate Threshold Variation vs. Ambient Temperature

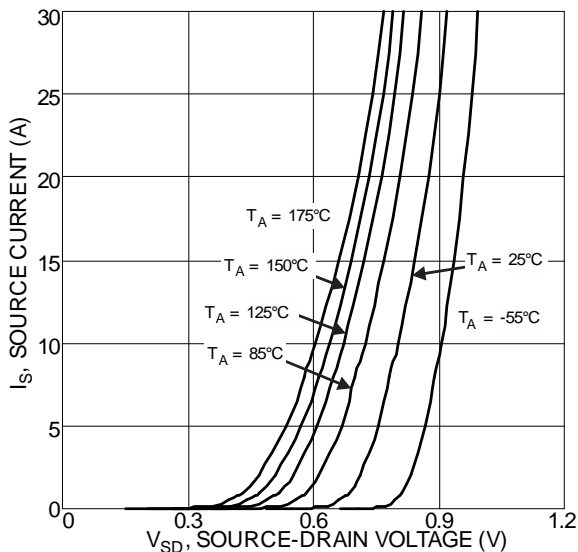


Figure 9 Diode Forward Voltage vs. Current

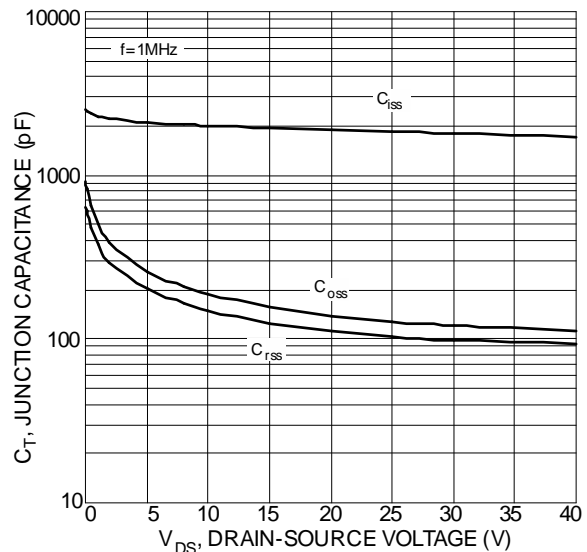


Figure 10 Typical Junction Capacitance

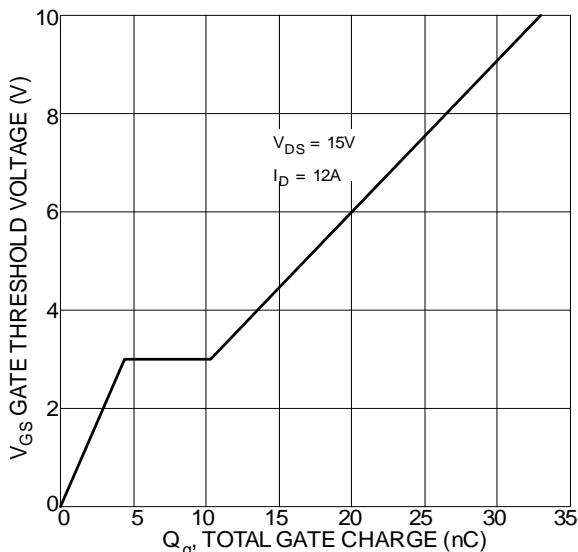


Figure 11 Gate Charge

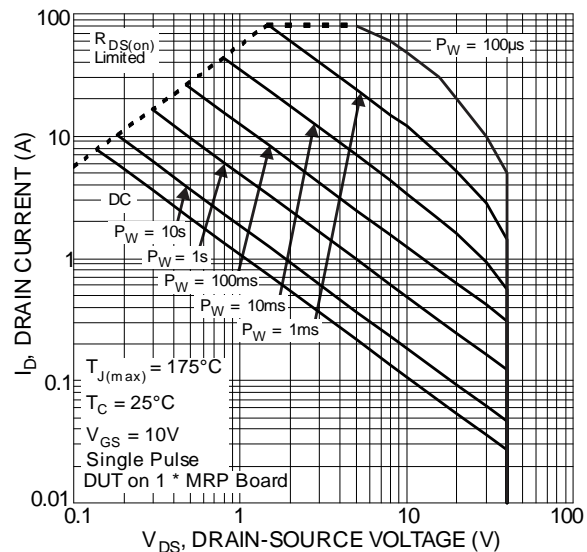
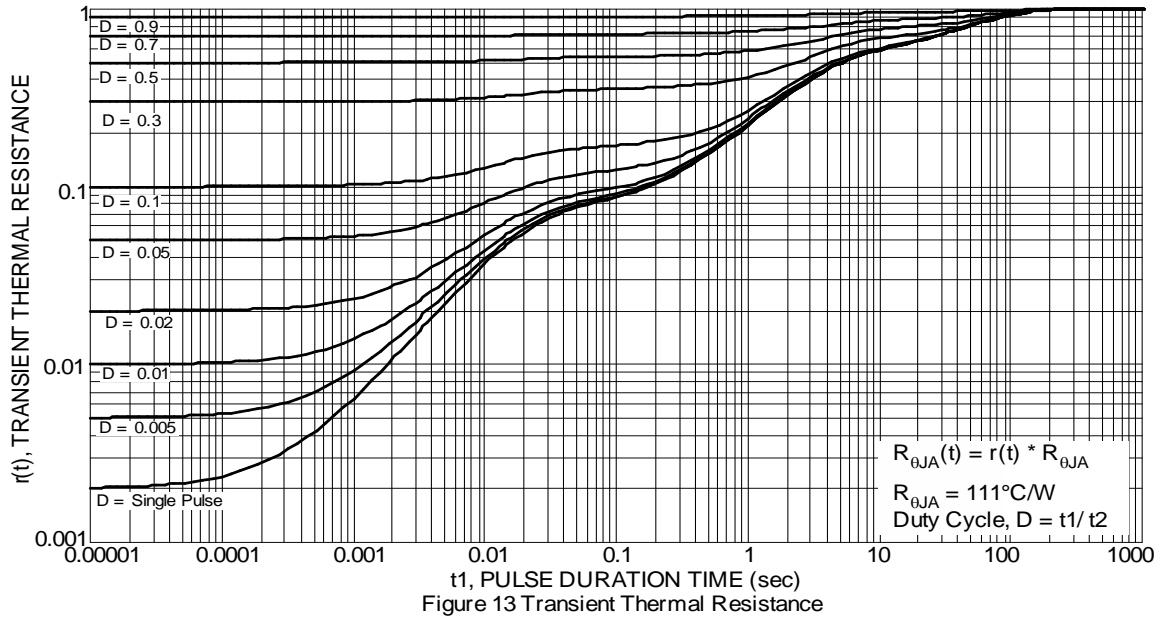


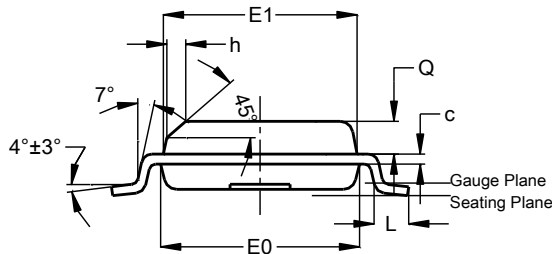
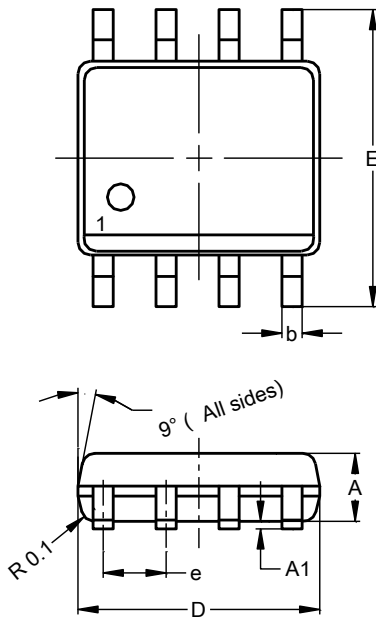
Figure 12 SOA, Safe Operation Area



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8

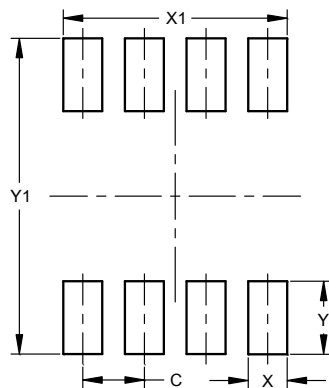


SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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